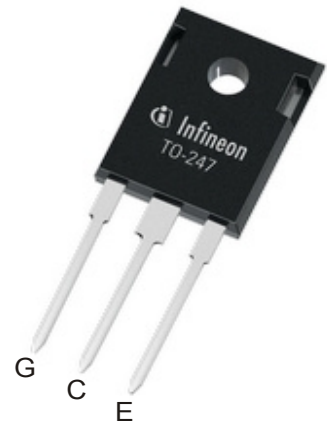
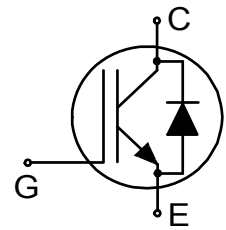


Resonant Switching Series

Reverse Conducting IGBT with monolithic body diode

Features:

- Offers high breakdown voltage of 1350V for improved reliability
- Powerful monolithic body diode with low forward voltage designed for soft commutation only
- TRENCHSTOP™ technology offering:
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - low V_{CEsat}
 - easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Low EMI
- Qualified according to JESD-022 for target applications
- Pb-free lead plating; RoHS compliant
- Halogen free (according to IEC 61249-2-21)
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



Applications:

- Inductive cooking
- Inverterized microwave ovens
- Resonant converters
- Soft switching applications



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IHW20N135R5	1350V	20A	1.65V	175°C	H20PR5	PG-TO247-3

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